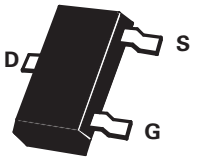
SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN3320F

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FEATURES

* 200 Volt V_{DS}
* $R_{DS(on)}$= 25Ω



SOT23

PARTMARKING DETAIL – MU

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	200	V
Continuous Drain Current at T_{amb}=25°C	I_D	60	mA
Pulsed Drain Current	I_{DM}	1	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation at T_{amb}=25°C	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	200		V	I_D=1mA, V_{GS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.0	3.0	V	I_D=1mA, V_{DS}= V_{GS}
Gate-Body Leakage	I_{GSS}		100	nA	V_{GS}=± 20V, V_{DS}=0V
Zero Gate Voltage Drain Current	I_{DSS}		10 50	µA µA	V_{DS}=200V, V_{GS}=0V V_{DS}=160V, V_{GS}=0V, T=125°C(2)
On-State Drain Current(1)	$I_{D(on)}$	250		mA	V_{DS}=25V, V_{GS}=10V
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		25	Ω	V_{GS}=10V,I_D=100mA
Forward Transconductance(1) (2)	g_{fs}	75		mS	V_{DS}=25V,I_D=100mA
Input Capacitance (2)	C_{iss}		45	pF	V_{DS}=25V, V_{GS}=0V, f=1MHz
Common Source Output Capacitance (2)	C_{oss}		18	pF	
Reverse Transfer Capacitance (2)	C_{rss}		5	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		5	ns	V_{DD}≈25V, I_D=100mA
Rise Time (2)(3)	t_r		7	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		6	ns	
Fall Time (2)(3)	t_f		6	ns	

(1) Measured under pulsed conditions. Width=300µs. Duty cycle ≤2% (2) Sample test.
(3) Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator